

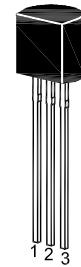
2SC3731

NPN Silicon Epitaxial Planar Transistor

for general purpose amplifier and high speed switching applications.

The transistor is subdivided into three groups, M, L and K, according to its DC current gain.

On special request, these transistors can be manufactured in different pin configurations.



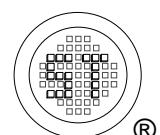
1. Emitter 2. Collector 3. Base
TO-92 Plastic Package

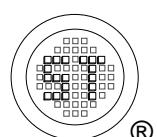
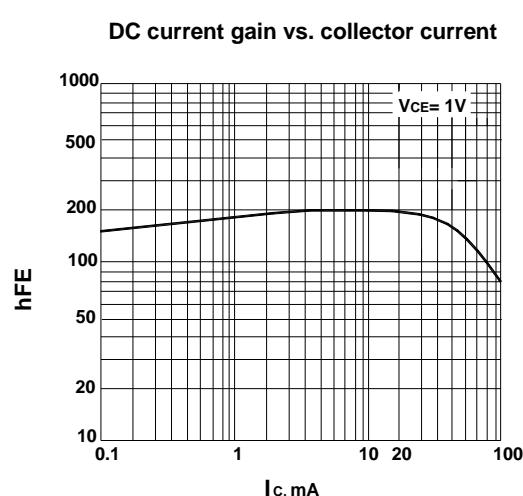
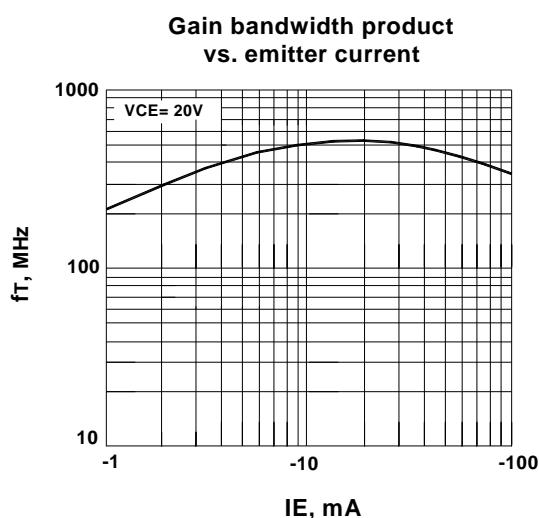
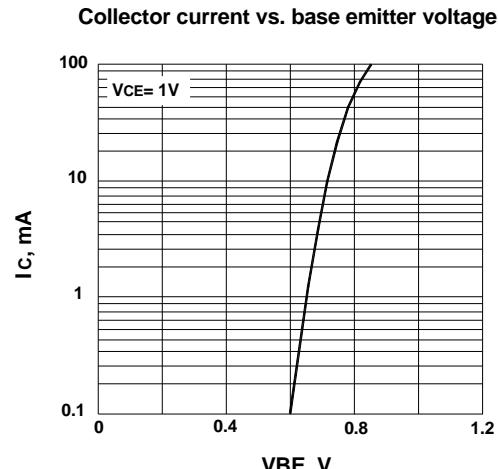
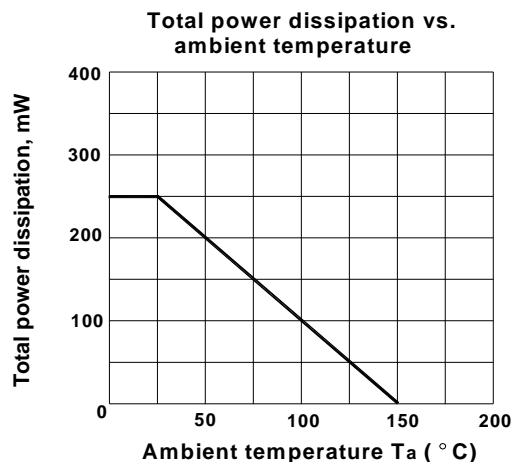
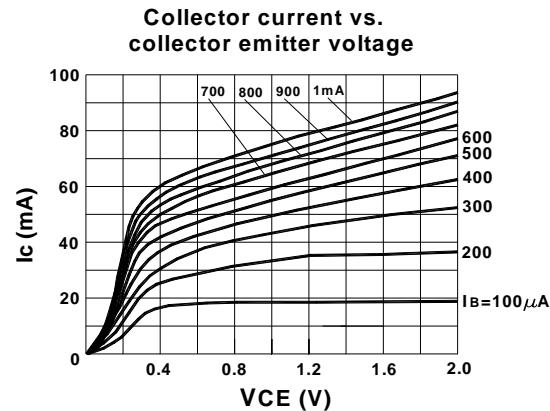
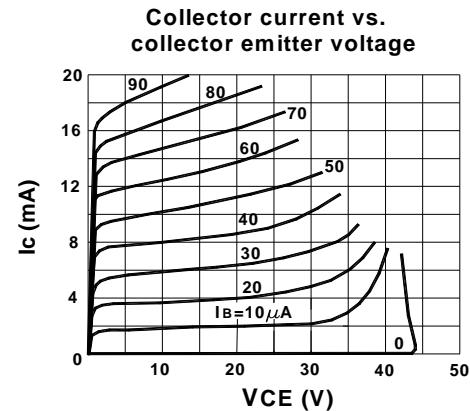
Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

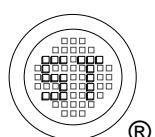
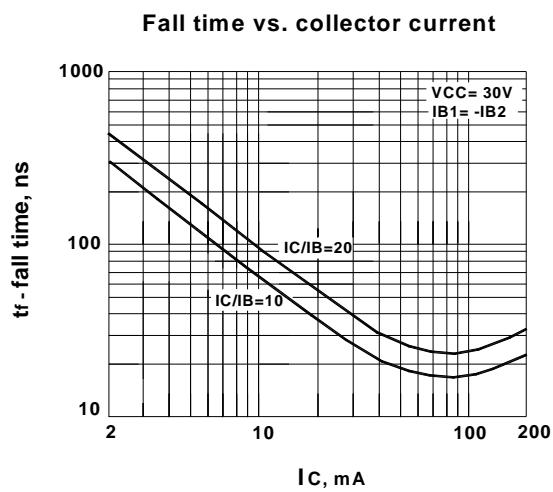
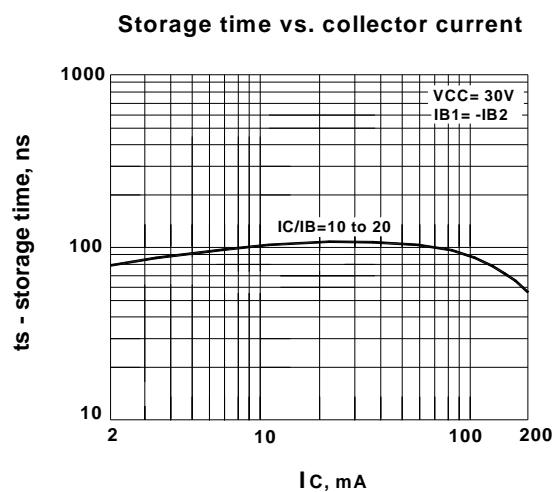
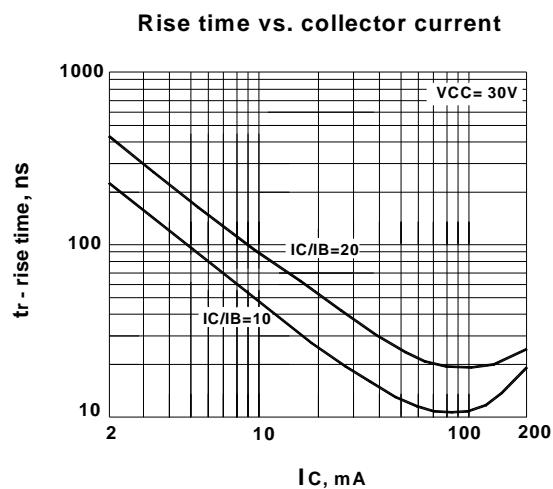
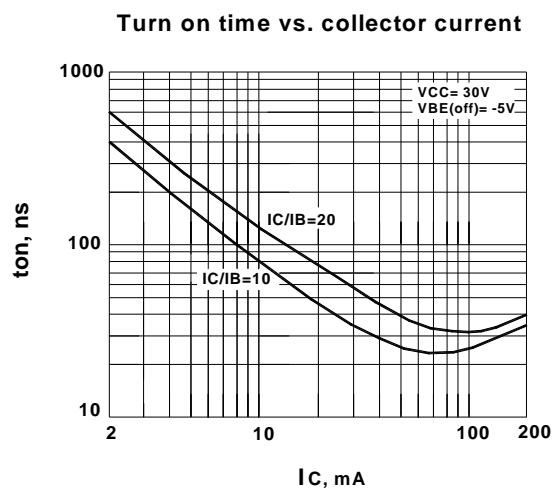
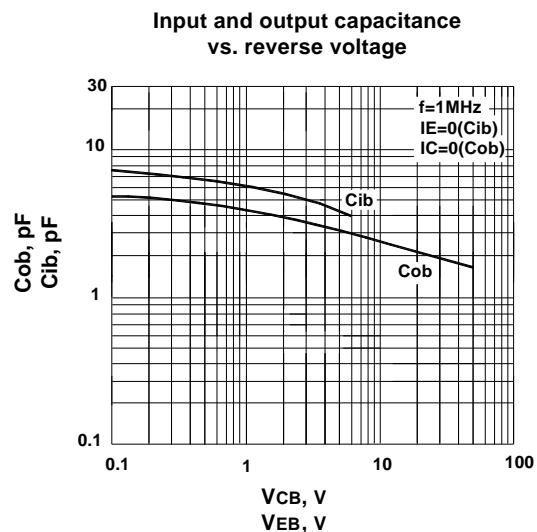
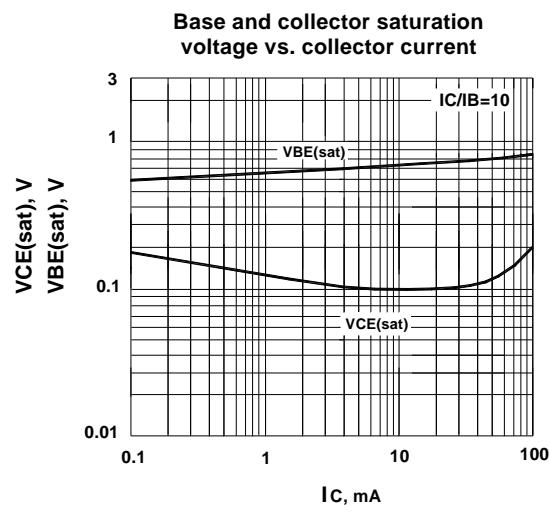
Parameter	Symbol	Value	Unit
Collector Base Voltage	V_{CBO}	60	V
Collector Emitter Voltage	V_{CEO}	40	V
Emitter Base Voltage	V_{EBO}	6	V
Collector Current	I_C	200	mA
Power Dissipation	P_{tot}	250	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 150	$^\circ\text{C}$

Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain at $V_{CE} = 1 \text{ V}$, $I_C = 10 \text{ mA}$	h_{FE}	75	-	150	-
	h_{FE}	100	-	200	-
	h_{FE}	150	-	300	-
	h_{FE}	25	80	-	-
Collector Base Cutoff Current at $V_{CB} = 30 \text{ V}$	I_{CBO}	-	-	0.1	μA
Emitter Base Cutoff Current at $V_{EB} = 3 \text{ V}$	I_{EBO}	-	-	0.1	μA
Collector Emitter Saturation Voltage at $I_C = 50 \text{ mA}$, $I_B = 5 \text{ mA}$	$V_{CE(sat)}$	-	0.12	0.3	V
Base Emitter Saturation Voltage at $I_C = 50 \text{ mA}$, $I_B = 5 \text{ mA}$	$V_{BE(sat)}$	-	0.8	0.95	V
Gain Bandwidth Product at $V_{CE} = 20 \text{ V}$, $-I_E = 10 \text{ mA}$, $f = 100 \text{ MHz}$	f_T	300	510	-	MHz
Output Capacitance at $V_{CB} = 5 \text{ V}$, $f = 1 \text{ MHz}$	C_{ob}	-	3	4	pF
Turn-on Time See test circuit	t_{on}	-	-	70	ns
Storage Time See test circuit	t_{stg}	-	100	200	ns
Turn-off Time See test circuit	t_{off}	-	-	250	ns







SWITCHING TIME TEST CIRCUIT

